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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/623,967	07/21/2003	Zheng Lu	MEMC 02-0400 (3053)	5338
321 · 7	7590 01/24/2005		EXAMINER	
SENNIGER POWERS LEAVITT AND ROEDEL ONE METROPOLITAN SOUARE			HITESHEW, FELISA CARLA	
	16TH FLOOR		ART UNIT	PAPER NUMBER
ST LOUIS, MO 63102			1765	
			DATE MAIL ED. 01/24/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	10/623,967	LU ET AL.	
Office Action Summary	Examiner	Art Unit	
	Felisa C. Hiteshew	1765	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence ad	idress
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	i6(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	nely filed s will be considered time the mailing date of this o D (35 U.S.C. § 133).	
Status			
Responsive to communication(s) filed on This action is FINAL. 2b)⊠ This Since this application is in condition for allowant closed in accordance with the practice under E	action is non-final. ace except for formal matters, pro		e ments is
Disposition of Claims	·		
4) ⊠ Claim(s) <u>1-23</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) <u>1,9,12 and 19</u> is/are rejected. 7) ⊠ Claim(s) <u>2-8,10,11,13-18 and 20-23</u> is/are objection and/or	vn from consideration.		
Application Papers			
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) access Applicant may not request that any objection to the or Replacement drawing sheet(s) including the correction 11) The oath or declaration is objected to by the Ex	epted or b) objected to by the Edrawing(s) be held in abeyance. See on is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 C	· •
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Applicati ity documents have been receive ı (PCT Rule 17.2(a)).	on No ed in this National	Stage
Attachment(s)	_		
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 10/623967. 	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate	O-152)

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Information Disclosure Statement

The Information Disclosure Statement under 37 C.F.R. 1.97 has been received and reviewed. However, the information disclosure is not deemed to be pertinent over the prior art of record.

Claim Rejections - 35 USC § 112

- 1. Claim 1 recites the limitation "... Czochralski process..." in line 2. There is insufficient antecedent basis for this limitation in the claim. Please insert the word --a -- before the word "Czochralski" for proper antecedence.
- 2. Claim 9 recites the limitation "... Czochralski process..." in line 2. There is insufficient antecedent basis for this limitation in the claim. Please insert the word -a - before the word "Czochralski" for proper antecedence.
- 3. Claim 121 recites the limitation "... Czochralski process..." in line 2. There is insufficient antecedent basis for this limitation in the claim. Please insert the word -a - before the word "Czochralski" for proper antecedence.
- 4. Claim 19 recites the limitation "... Czochralski process..." in line 2. There is insufficient antecedent basis for this limitation in the claim. Please insert the word
 - -a - before the word "Czochralski" for proper antecedence.

Allowable Subject Matter

5. As allowable subject matter has been indicated, applicant's reply must either comply with all formal requirements or specifically traverse each requirement not complied with. See 37 CFR 1.111(b) and MPEP § 707.07(a).

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6. Claims 2-8, 10,11, 13-18 and 20-23 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

7. The following is a statement of reasons for the indication of allowable subject matter: The most relevant prior art of reference is that of U.S. Patent No. 6, 503,322 (Schrenker, et al). However, it does not teach nor fairly suggest singularly or in any combination thereof a method or apparatus for producing a crystal growing apparatus for optimizing a cooling rate of a monocrystalline ingot grown according to the Czochralski process, said crystal growing apparatus having a heated crucible containing a semiconductor melt from which the ingot is grown, said ingot being grown on a seed crystal pulled from the melt, said crystal growing apparatus further having a receiving chamber into which the ingot is pulled, said ingot being pulled along a generally longitudinal path toward the receiving chamber, said method comprising determining a first temperature of the ingot when the ingot is at a first position along the path; determining a second temperature of the ingot when the ingot is at a second position along the path, said first and second positions being separated by a distance D along the pate; determining a cooling rate of the ingot as a function of a difference between the first temperature and the second temperature relative to an amount of time for pulling the ingot the distance D; generating a signal representative of an error between a target cooling rate of the ingot and the determined cooling rate of the ingot; and adjusting one or more post-growth processing parameters as a function of the error signal thereby to control the cooling rate of the ingot.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Felisa Hiteshew whose telephone number is (571) 272-1463. The examiner can normally be reached on Mondays through Thursdays from 5:30 AM to 3:00 PM. and second Fridays from 5:30 AM to 2:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton, can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-1463.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system. see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866- 217-9197 (toll-free).

FELISA HITESHEW
PRIMARY EXAMINER